

Amendments to the Specification:

Please replace the paragraph beginning at page 11, line 13, with the following amended paragraph:

Further, an oxide film is removed by immersing the test pieces for 30 seconds in a 0.5% hydrofluoric acid solution. In addition, anisotropic etching is performed by immersing the test pieces in a KOH / IPA solution for 30 seconds. The anisotropic etching makes it possible to observe crystal orientation in the grains, as well as grain boundaries, by an optical microscope. The surfaces of the test pieces were observed here by using an optical microscope (bright field reflection mode, 200x magnification) after performing the anisotropic etching, and the results are shown in Figs. 17A and 17B. Fig. 17A is a photograph showing the results when Ar plasma exposure is performed, and Fig. 17B is a photograph showing the results when Ar plasma exposure is not performed. Further, Figs. 18B and 18A are schematic diagrams of Figs. 17B and 17A, respectively. It can be seen that the grain is smaller in Figs. 17A and 18A compared to grain size of Figs. 17B and 18B. The grain boundaries in Figs. 17A and 18A are vague as compared with those of Figs. 17B and 18B, and it is thought that the reason for this is that the grain size is small, and that overlapping develops with the small grains.